TOSHIBA

MICROWAVE SEMICONDUCTOR

TECHNICAL DATA

MICROWAVE POWER GaAs FET

TIM5359-4UL

FEATURES

- **HIGH POWER**
  P1dB=36.5dBm at 5.3GHz to 5.9GHz
- **HIGH GAIN**
  G1dB=10.5dB at 5.3GHz to 5.9GHz
- **BROAD BAND INTERNALLY MATCHED FET**
- **HERMETICALLY SEALED PACKAGE**

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P_{1dB}	V_{DS}= 10V f = 5.3 to 5.9GHz	dBm	35.5	36.5	—
Power Gain at 1dB Gain Compression Point	G_{1dB}		dB	9.5	10.5	—
Drain Current	I_{DS1}		A	—	1.1	1.3
Gain Flatness	ΔG		dB	—	—	±0.6
Power Added Efficiency	η_{add}		%	—	37	—
3rd Order Intermodulation Distortion	IM_3	Two-Tone Test Po= 25.5dBm (Single Carrier Level)	dBc	-44	-47	—
Drain Current	I_{DS2}		A	—	1.1	1.3
Channel Temperature Rise	ΔTch	(VDS X IDS +Pin- P_{1dB}) X $R_{th(c-c)}$	°C	—	—	80

Recommended gate resistance(Rg) : Rg= 150 Ω(MAX.)

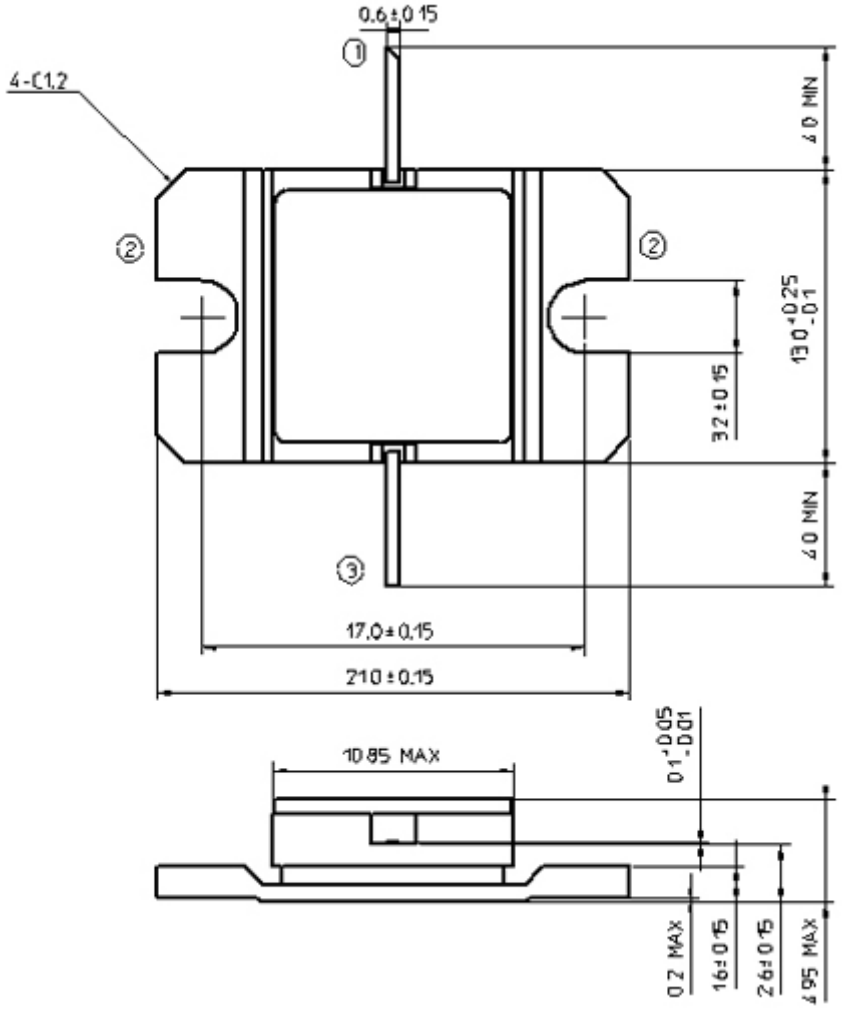
ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	V_{DS}= 3V I_{DS}= 1.5A	mS	—	900	—
Pinch-off Voltage	V_{GSoff}	V_{DS}= 3V I_{DS}= 15mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	I_{DSS}	V_{DS}= 3V V_{GS}= 0V	A	—	2.6	—
Gate-Source Breakdown Voltage	V_{GSO}	I_{GS}= -50μA	V	-5	—	—
Thermal Resistance	$R_{th(c-c)}$	Channel to Case	°C/W	—	4.5	6.0

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	3.5
Total Power Dissipation (Tc= 25 °C)	PT	W	25
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-11D1B)



Unit in mm

(1) Gate

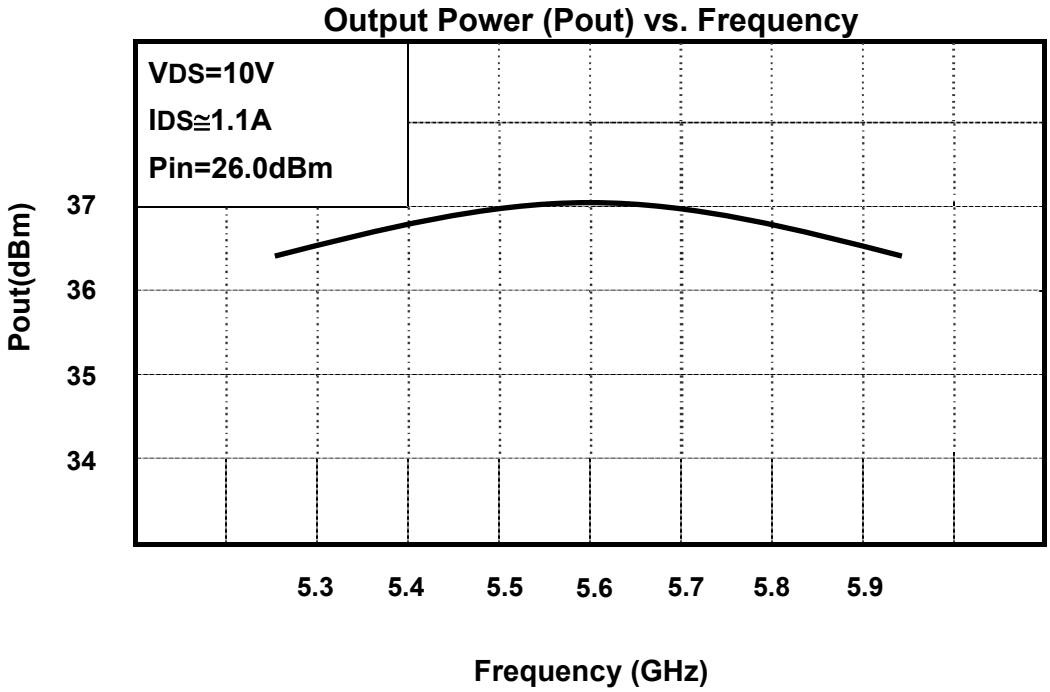
(2) Source

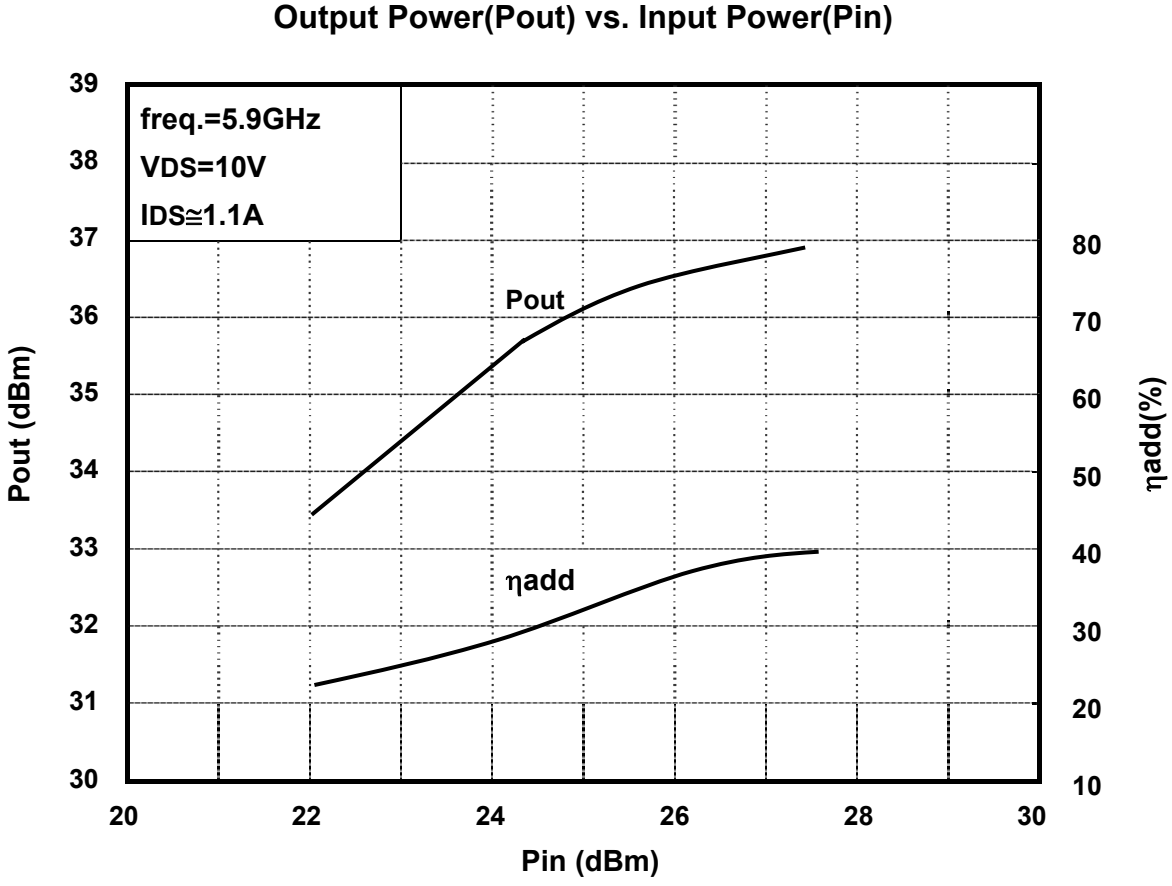
(3) Drain

HANDLING PRECAUTIONS FOR PACKAGE MODEL

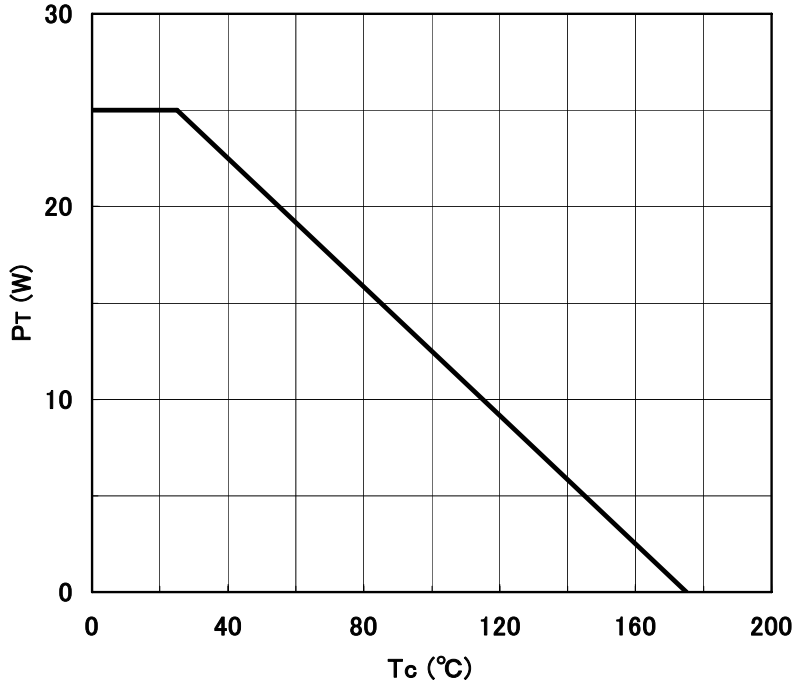
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF PERFORMANCE





Power Dissipation vs. Case Temperature



IM3 vs. Output Power Characteristics